



#### P-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

V <sub>(BR)DSS</sub>	Rea(an) man	ID
V (BR)DSS	R <sub>DS(on) max</sub>	T <sub>C</sub> = +25°C
-40V	11mΩ @ V <sub>GS</sub> = -10V	-35A
-40 V	15mΩ @ V <sub>GS</sub> = -4.5V	-30A

## Description

This new generation MOSFET has been designed to minimize the onstate resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

- DC-DC Converters
- Power management functions
- Backlighting

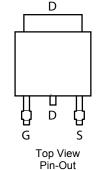
## **Features and Benefits**

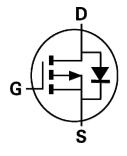
- 100% Unclamped Inductive Switch (UIS) test in production
- Low on-resistance
- Fast switching speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Finish annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208<sup>3</sup>
- Weight: 0.33 grams (approximate)







Equivalent Circuit

## Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
DMP4015SK3-13	Standard	TO252	2,500/Tape & Reel
DMP4015SK3Q-13	Automotive	TO252	2,500/Tape & Reel

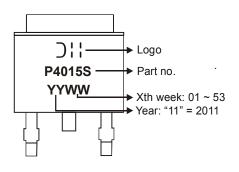
Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

 See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http"//www.diodes.com/products/packages.html

## **Marking Information**





## Maximum Ratings (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V <sub>DSS</sub>	-40	V		
Gate-Source Voltage		V <sub>GSS</sub>	±25	V	
Continuous Drain Current (Note 5) $V_{GS}$ = -10V	Steady State	T <sub>C</sub> = +25°C T <sub>C</sub> = +70°C	ID	-35 -27	А
Continuous Drain Current (Note 5) V <sub>GS</sub> = -10V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	ID	-14 -11	А
	t<10s	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	ID	-22 -18	А
Pulsed Drain Current ( $10\mu$ s pulse, duty cycle = 1%)	•	I <sub>DM</sub>	-100	A	
Maximum Body Diode Forward Current (Note 5)			ls	-5.5	Α
Avalanche Current (Note 6)	I <sub>AS</sub>	-57	A		
Avalanche Energy (Note 6)			E <sub>AS</sub>	162	mJ

## Thermal Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Bower Dissinction (Note E)	T <sub>A</sub> = +25°C	D-	3.5	W
Total Power Dissipation (Note 5)	T <sub>A</sub> = +70°C	PD	2.2	
Thermal Decistores Junction to Ambient (Note 5)	Steady state	D	36	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	15	
Thermal Resistance, Junction to Case (Note 5)	Steady state	R <sub>θJC</sub>	4.5	
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

## Electrical Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)						÷	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-40	—		V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	—	-1	μA	$V_{DS}$ = -40V, $V_{GS}$ = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	_	—	±100	nA	$V_{GS}$ = ±25V, $V_{DS}$ = 0V	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1.5	-2.0	-2.5	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance		_	7	11		V <sub>GS</sub> = -10V, I <sub>D</sub> = -9.8A	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	9	15	mΩ	$V_{GS}$ = -4.5V, $I_{D}$ = -9.8A	
Forward Transfer Admittance	Y <sub>fs</sub>	_	26	_	S	V <sub>DS</sub> = -20V, I <sub>D</sub> = -9.8A	
Diode Forward Voltage	V <sub>SD</sub>	_	-0.7	-1.0	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	4234	—			
Output Capacitance	Coss	_	1036	_	pF	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	526	_			
Gate Resistance	R <sub>G</sub>	_	7.77	_	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz	
Total Gate Charge	Qq		47.5	—			
Gate-Source Charge	Q <sub>gs</sub>	_	14.2	_	nC	V <sub>DS</sub> = -20V, V <sub>GS</sub> = -5V I <sub>D</sub> = -9.8A	
Gate-Drain Charge	Q <sub>qd</sub>		13.5	—		ID9.0A	
Turn-On Delay Time	t <sub>D(on)</sub>		13.2			V <sub>GS</sub> = -10V, V <sub>DD</sub> = -20V,	
Turn-On Rise Time	tr		10.0		1		
Turn-Off Delay Time	t <sub>D(off)</sub>		302.7		ns	$R_G = 6\Omega$ , $I_D = -1A$	
Turn-Off Fall Time	tf		137.9		1		

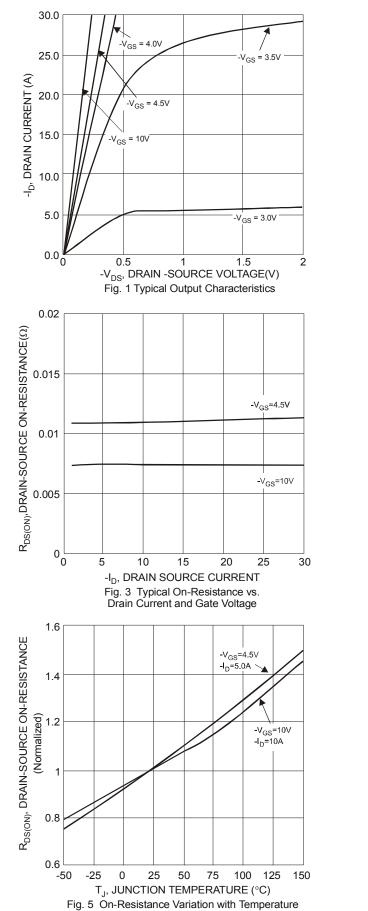
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

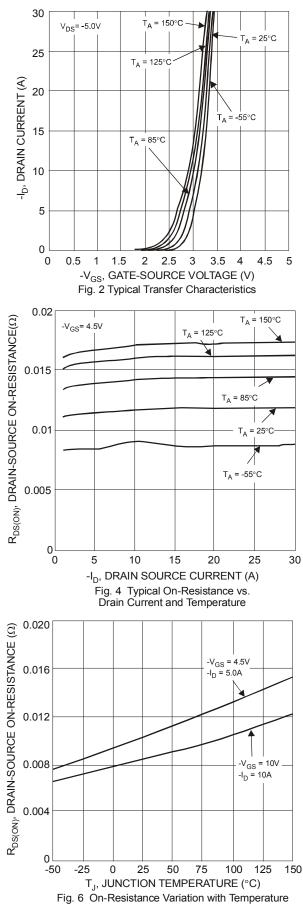
6. UIS in production with L = 0.1mH,  $T_J$  = +25°C.

7 .Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to production testing.

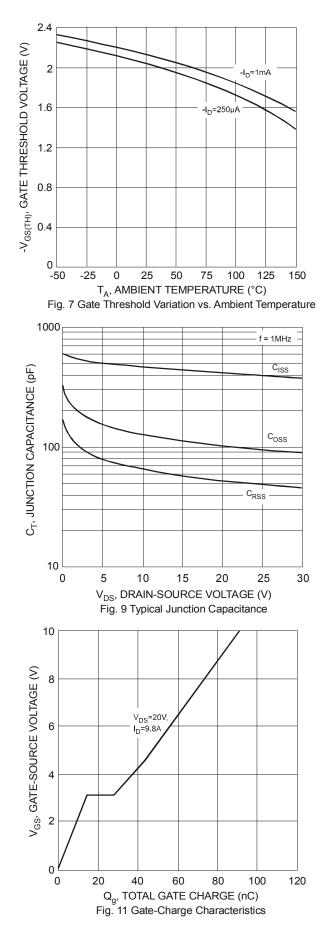


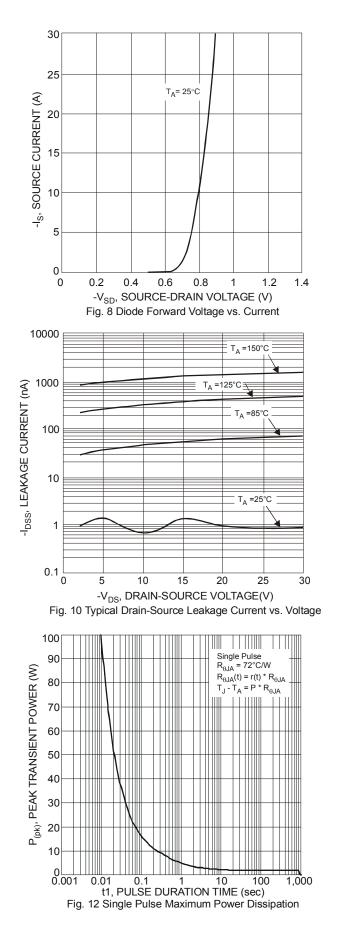




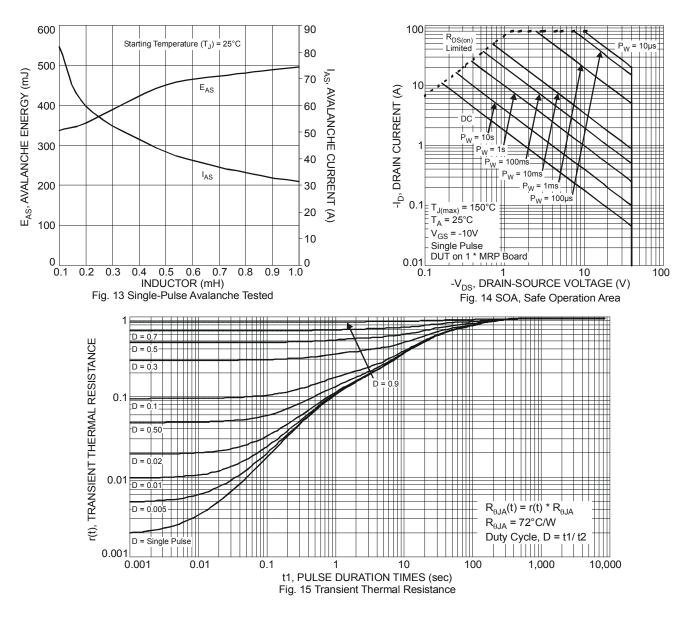
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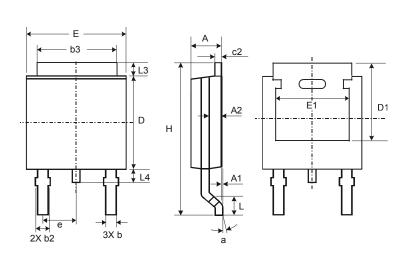






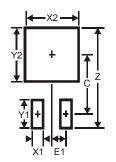


## Package Outline Dimensions



TO252					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
c2	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	_	_	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
Η	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

## Suggested Pad Layout



Dimensions	Value (in mm)
Z	11.6
X1	1.5
X2	7.0
Y1	2.5
Y2	7.0
С	6.9
E1	2.3



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